

Silicon NPN Power Transistors

2SC792

DESCRIPTION

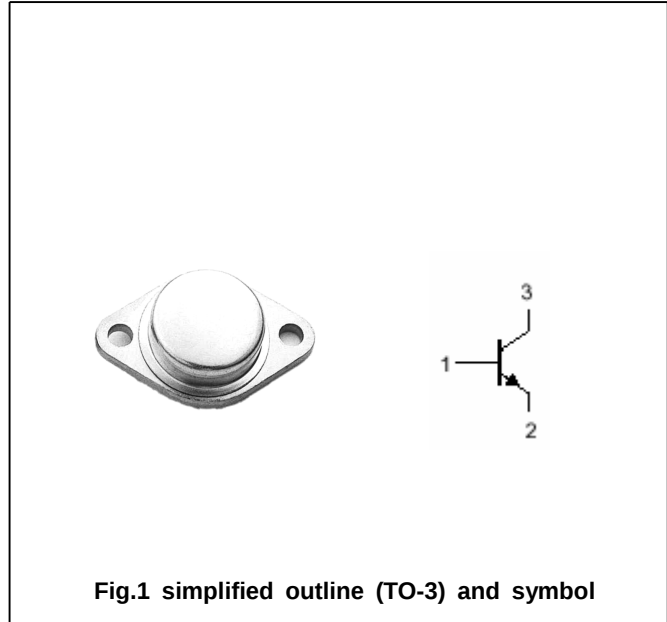
- With TO-3 package
- High breakdown voltage

APPLICATIONS

- For voltage regulator,inverter,switching mode power supply applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

**Absolute maximum ratings(Ta=?)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	400	V
V_{CEO}	Collector-emitter voltage	Open base	300	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		1.5	A
P_C	Collector power dissipation	$T_C=25^\circ$	50	W
T_j	Junction temperature		150	°
T_{stg}	Storage temperature		-55~150	°

Silicon NPN Power Transistors

2SC792

CHARACTERISTICS

Tj=25? unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=10mA ; I_B=0$	300			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=1mA ; I_C=0$	5			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=1.5A ; I_B=0.3A$			5.0	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=1.5A ; I_B=0.3A$			1.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=300V ; I_E=0$			50	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=5V ; I_C=0$			50	μA
h_{FE}	DC current gain	$I_C=0.3A ; V_{CE}=10V$	30		200	
f_T	Transition frequency	$I_C=0.1A ; V_{CE}=10V$		10		MHz

Silicon NPN Power Transistors

2SC792

PACKAGE OUTLINE

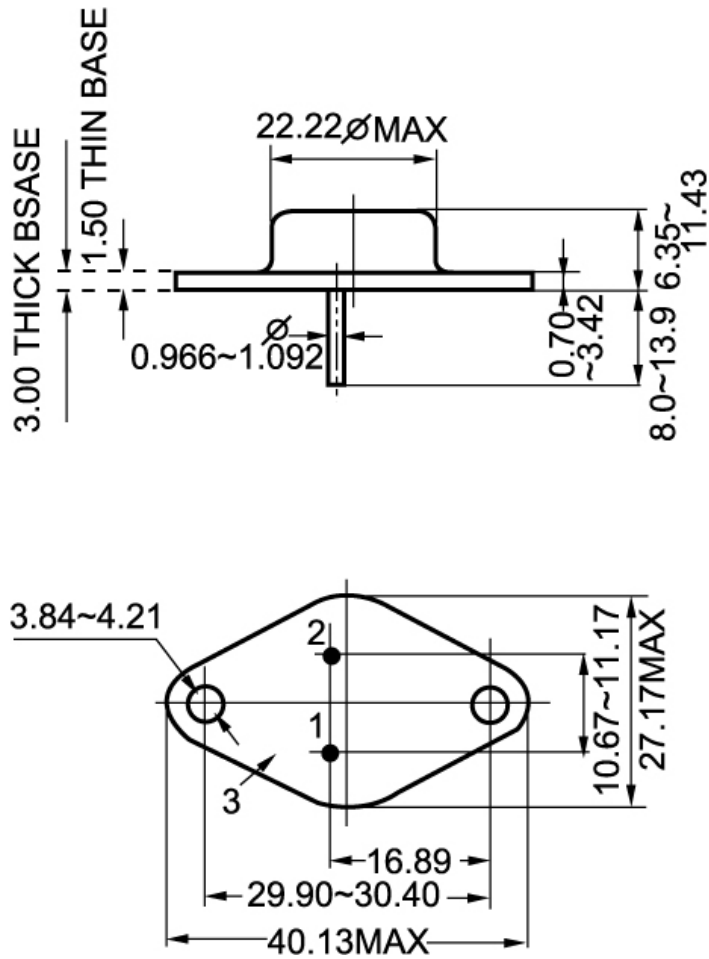


Fig.2 outline dimensions (unindicated tolerance:±0.1mm)